

PERFORMANCE SPECIFICATION

SEMICONDUCTOR DEVICE, FIELD EFFECT RADIATION HARDENED
(TOTAL DOSE AND SINGLE EVENT EFFECTS)
TRANSISTOR, N-CHANNEL, SILICON TYPES 2N7468U2 AND 2N7469U2
JANTXVR, F, G AND H AND JANSR, F, G AND H

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for an N-channel, enhancement-mode, MOSFET, radiation hardened (total dose and single event effects (SEE)), power transistor. Four levels of product assurance are provided for each device type as specified in MIL-PRF-19500, with avalanche energy maximum rating (E_{AS}) and maximum avalanche current (I_{AS}).

1.2 Physical dimensions. See figure 1, (surface mount, U2).

1.3 Maximum ratings. $T_A = +25^\circ\text{C}$, unless otherwise specified.

Type	P_T (1) $T_C = +25^\circ\text{C}$	P_T (1) $T_A = +25^\circ\text{C}$	V_{DS}	V_{DG}	V_{GS}	I_{D1} (2) $T_C = +25^\circ\text{C}$	I_{D2} $T_C = +100^\circ\text{C}$	I_S	I_{DM} (3)	T_J and T_{STG}	V_{ISO} 70,000 ft. altitude
	<u>W</u>	<u>W</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A (pk)</u>	<u>°C</u> -55 to +150	<u>V dc</u> N/A
2N7468U2	250	2.5	60	60	± 20	75	45	75	300		
2N7469U2	250	2.5	100	100	± 20	75	45	75	300		

(1) Derate linearly $2.4 \text{ W}/^\circ\text{C}$ for $T_C > +25^\circ\text{C}$; $P_T = (T_{jmax} - T_C)/R_{\theta JC}$.

(2) $I_D = ((T_{jmax} - T_C)/((R_{\theta JC}) \times (f_{DS(on)} \text{ at } T_{jmax})))^{1/2}$.

(3) $I_{DM} = 4 \times I_{D1}$; I_{D1} as calculated by footnote (2).

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Defense Supply Center, Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43216-5000, by using the Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

1.4 Primary electrical characteristics at $T_C = +25^\circ\text{C}$.

Type	Min $V_{(BR)DSS}$ $V_{GS} = 0$ $I_D = 1.0\text{mA}$ dc	$V_{GS(TH)1}$ $V_{DS} \geq V_{GS}$ $I_D = 1.0\text{mA}$ dc	Max I_{DSS1} $V_{GS} = 0$ $V_{DS} = 80$ percent of rated V_{DS}	Max $r_{DS(on)}$ (1) $V_{GS} = 12\text{V}$, $I_D = I_{D2}$		$R_{\theta JC}$ Max	E_{AS}
				$T_J = +25^\circ\text{C}$	$T_J = +150^\circ\text{C}$		
	<u>V dc</u>	<u>V dc</u> Min Max	<u>μA dc</u>	<u>Ω</u>	<u>Ω</u>	<u>$^\circ\text{C/W}$</u>	<u>mJ</u>
2N7468U2	60	2.0 4.0	10	0.0056	0.011	0.50	500
2N7469U2	100	2.0 4.0	10	0.012	0.022	0.50	363

(1) Pulsed (see 4.5.1).

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation (see 6.2).

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

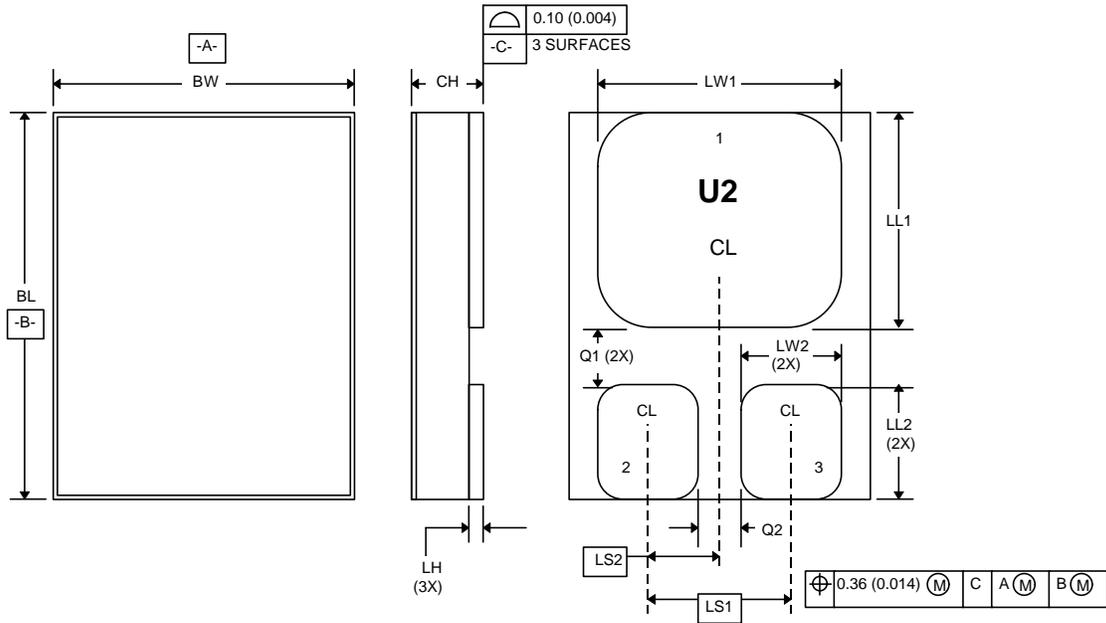
STANDARD

DEPARTMENT OF DEFENSE

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Unless otherwise indicated, copies of the above specifications, standards, and handbooks are available from the Document Automation and Production Services (DAPS), Building 4D (DPM-DODSSP), 700 Robbins Avenue, Philadelphia, PA 19111-5094.)

2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.



Symbol	Dimensions			
	Inches		Millimeters	
	Min	Min	Min	Max
BL	0.684	0.684	17.38	0.696
BW	0.519	0.519	13.19	0.531
CH				0.142
LH	0.010	0.010	0.26	0.020
LW1	0.434	0.434	11.03	0.446
LW2	0.134	0.134	3.41	0.146
LL1	0.469	0.469	11.92	0.481
LL2	0.151	0.151	3.84	0.163
LS1	0.240 BSC		0.240 BSC	
LS2	0.120 BSC		0.120 BSC	
Q1	0.035	0.035	0.89	
Q2	0.050	0.050	1.27	
TERM 1	Drain			
TERM 2	Gate			
TERM 3	Source			

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for information only.
3. The lid shall be electrically isolated from the drain, gate and source.
4. In accordance with ANSI Y14.5M, diameters are equivalent to ϕx symbology.

FIGURE 1. Dimensions and configuration (U2).

3. REQUIREMENTS

3.1 General. The requirements for acquiring the product described herein shall consist of this document and MIL-PRF-19500.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in MIL-PRF-19500, and figure 1 (U2) herein. Methods used for electrical isolation of the terminals shall employ materials that contain a minimum of 90 percent Al_2O_3 (ceramic).

3.4.1 Lead finish. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.5 Marking. Marking shall be in accordance with MIL-PRF-19500.

3.6 Electrostatic discharge protection. The devices covered by this specification require electrostatic discharge protection (see 3.6.1).

3.6.1 Handling. MOS devices must be handled with certain precautions to avoid damage due to the accumulation of static charge. However, the following handling practices are recommended (see 3.5).

- a. Devices should be handled on benches with conductive handling devices.
- b. Ground test equipment, tools and personnel handling devices.
- c. Do not handle devices by the leads.
- d. Store devices in conductive foam or carriers.
- e. Avoid use of plastic, rubber or silk in MOS areas.
- f. Maintain relative humidity above 50 percent if practical.
- g. Care should be exercised during test and troubleshooting to apply not more than maximum rated voltage to any lead.
- h. Gate must be terminated to source, $R \leq 100 \text{ k}\Omega$, whenever bias voltage is applied drain to source.

3.7 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3 and 1.4 herein.

3.8 Electrical test requirements. The electrical test requirements shall be the subgroups as specified in group A, table I herein.

3.9 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4 and tables I, II, and III).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500 and as specified herein. Alternate flow is allowed for qualification inspection in accordance with figure 4 of MIL-PRF-19500.

4.2.1 Group E inspection. Group E inspection shall be conducted in accordance with MIL-PRF-19500 and table III herein.

4.2.1.1 SEE. Design capability shall be tested on the initial qualification and thereafter whenever a major die design or process change is introduced. (See the design safe operation area figures herein.) End-point measurements shall be in accordance with table III herein.

4.3 Screening (JANS, JANTX, and JANTXV). Screening shall be in accordance with table IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

MIL-PRF-19500/673

Screen (see table IV of MIL-PRF-19500)	Measurement	
	JANS	JANTX and JANTXV
(1)	Method 3470, E _{AS} test (see 4.5.4)	Method 3470, E _{AS} test (see 4.5.4)
(1)	Method 3161, thermal impedance (see 4.5.3)	Method 3161, thermal impedance (see 4.5.3)
(1)	Gate stress test (see 4.5.5)	Gate stress test (see 4.5.5)
(2) 9	Subgroup 2 of table I herein I _{DSS1} , I _{GSS} as a minimum	Not applicable
10	Method 1042 of MIL-STD-750, test condition B	Method 1042 of MIL-STD-750, test condition B
11	I _{GSSF1} , I _{GSSR1} , I _{DSS1} , r _{DS(ON)} , V _{GS(TH)} Subgroup 2 of table I herein. $\Delta I_{GSSF1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{GSSR1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{DSS1} = \pm 10 \text{ } \mu\text{A dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$	I _{GSSF1} , I _{GSSR1} , I _{DSS1} , r _{DS(ON)} , V _{GS(TH)} Subgroup 2 of table I herein.
12	Method 1042 of MIL-STD-750, test condition A	Method 1042 of MIL-STD-750, test condition A
13	Subgroups 2 and 3 of table I herein $\Delta I_{GSSF1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{GSSR1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{DSS1} = \pm 10 \text{ } \mu\text{A dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta r_{DS(ON)1} = \pm 20 \text{ percent of initial value.}$ $\Delta V_{GS(TH)1} = \pm 20 \text{ percent of initial value.}$	Subgroups 2 and 3 of table I herein $\Delta I_{GSSF1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{GSSR1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{DSS1} = \pm 10 \text{ } \mu\text{A dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta r_{DS(ON)1} = \pm 20 \text{ percent of initial value.}$ $\Delta V_{GS(TH)1} = \pm 20 \text{ percent of initial value.}$

- (1) Shall be performed anytime before screen 10.
(2) Shall be performed after E_{AS} test, thermal impedance test, and gate stress test.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500. Alternate flow is allowed for conformance inspection in accordance with figure 4 of MIL-PRF-19500.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with table V of MIL-PRF-19500 and table I herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VIa (JANS) and table VIb (JANTX and JANTXV) of MIL-PRF-19500, and as follows. Electrical measurements (end-points) shall be in accordance with table I, group A, subgroup 2 herein.

4.4.2.1 Group B inspection, table VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
3	1051	Test condition G, 100 cycles.
3	2077	SEM.
4	1042	Intermittent operation life, condition D, 2,000 cycles. No heat sink or forced-air cooling on the device shall be permitted during the on cycle. $t_{on} = 30$ seconds minimum.
5	1042	Accelerated steady-state gate bias, condition B, $V_{GS} =$ rated; $T_A = +175^\circ\text{C}$, $t = 24$ hours minimum; or $T_A = +150^\circ\text{C}$, $t = 48$ hours minimum.
5	1042	Accelerated steady-state reverse bias, condition A, $V_{DS} =$ rated; $T_A = +175^\circ\text{C}$, $t = 120$ hours minimum; or $T_A = +150^\circ\text{C}$, $t = 240$ hours minimum.
5	2037	Bond strength (Al-Au die interconnects only), test condition A.
6	3161	Thermal resistance, see 4.5.2.

4.4.2.2 Group B inspection, table VIb (JANTX and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
2	1051	Test condition G, 25 cycles.
3	1042	Intermittent operation life, condition D, 2,000 cycles. No heat sink or forced-air cooling on the device shall be permitted during the on cycle. $t_{on} = 30$ seconds minimum.
5 and 6		Not applicable.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VII of MIL-PRF-19500 and as follows. Electrical measurements (end-points) shall be in accordance with table I, group A, subgroup 2 herein.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
2	2036	Terminal strength is not applicable.
6	1042	Intermittent operation life, condition D, 2,000 cycles. No heat sink or forced-air cooling on the device shall be permitted during the on cycle. $t_{on} = 30$ seconds minimum.

4.4.4 Group D inspection. Group D inspection shall be conducted in accordance with table VIII of MIL-PRF-19500 and table II herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

4.5.2 Thermal resistance. Thermal resistance measurements shall be performed in accordance with method 3161 of MIL-STD-750. The maximum limit of $R_{\theta JC} = 0.42 \text{ }^\circ\text{C/W}$. The following parameters shall apply:

- a. Measuring current (I_M)..... 10 mA.
- b. Drain heating current (I_H)..... 13.33 A.
- c. Heating time (t_H)..... Steady-state (see method 3161 of MIL-STD-750).
- d. Drain-source heating voltage (V_H)..... 15 V.
- e. Measurement time delay (t_{MD})..... 30 to 60 μs .
- f. Sample window time (t_{SW})..... 10 μs maximum.

4.5.3 Thermal response ($Z_{\theta JC}$ measurement). The $Z_{\theta JC}$ measurement (or equivalent ΔV_{SD} measurement) shall be performed in accordance with method 3161 of MIL-STD-750. The maximum limit (not to exceed figure 2, thermal impedance curves and the group A, subgroup 2 limits) for $Z_{\theta JC}$ in screening (table IV of MIL-PRF-19500) shall be derived by each vendor by means of statistical process control. When the process has exhibited control and capability, the capability data shall be used to establish the fixed limit. In addition to screening, once a fixed limit has been established, monitor all future sealing lots using a random five piece sample from each lot, to be plotted on the applicable X and R chart. If a lot exhibits an out of control condition, the entire lot shall be removed from the line and held for engineering evaluation and disposition. This procedure may be used in lieu of an in line process monitor.

- a. Measuring current (I_M)..... 10 mA.
- b. Drain heating current (I_H)..... 13.33 A.
- c. Heating time (t_H)..... 20 ms.
- d. Drain-source heating voltage (V_H)..... 15 V.
- e. Measurement time delay (t_{MD})..... 30 - 60 μs .
- f. Sample window time (t_{SW})..... 10 μs maximum.

4.5.4 Single pulse avalanche energy (E_{AS}).

- a. Peak current, $I_{AS} = I_{D1}$.
- b. Inductance, $L = (2 * E_{AS} / (I_{D1})^2) * ((V_{BR} - V_{DD}) / V_{BR})$ mH minimum.
- c. Gate to source resistor, $R_{GS}: 25 \Omega \leq R_{GS} \leq 200 \Omega$.
- d. Supply voltage, $V_{DD} = 25 \text{ V dc}$, except $V_{DD} = 50 \text{ V dc}$ for 2N7469U2.
- e. Initial case temperature, $T_C = +25^\circ\text{C}, -5^\circ\text{C}, +10^\circ\text{C}$.
- f. Gate voltage, $V_{GS} = 12 \text{ V dc}$.
- g. Number of pulses to be applied: 1 pulse minimum.

TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Condition		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>						
Thermal impedance <u>2/</u>	3161	See 4.5.3	$Z_{\theta JC}$	0.37		°C/W
Breakdown voltage drain to source	3407	$V_{GS} = 0V$, $I_D = 1 \text{ mA dc}$, bias condition C	$V_{(BR)DSS}$			
2N7468U2				60		V dc
2N7469U2				100		V dc
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$, $I_D = 1 \text{ mA dc}$	$V_{GS(TH)1}$	2.0	4.0	V dc
Gate current	3411	$V_{GS} = \pm 20V \text{ dc}$, bias condition C, $V_{DS} = 0V$	I_{GSS1}		± 100	nA dc
Drain current	3413	$V_{GS} = 0V \text{ dc}$, bias condition C, $V_{DS} = 80 \text{ percent of rated } V_{DS}$,	I_{DSS1}		10	$\mu\text{A dc}$
Static drain to source "ON" state resistance	3421	$V_{GS} = 12V \text{ dc}$, condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(ON)1}$			
2N7468U2					0.0056	Ω
2N7469U2					0.012	Ω
Forward voltage	4011	$V_{GS} = 0V \text{ dc}$, condition A, pulsed (see 4.5.1), $I_D = I_{D1}$	V_{SD}			
2N7468U2					1.3	V dc
2N7469U2					1.2	V dc

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Condition		Min	Max	
<u>Subgroup 3</u>						
High temperature operation		$T_C = T_J = +125^\circ\text{C}$				
Gate current	3411	$V_{GS} = \pm 20\text{V dc}$, bias condition C, $V_{DS} = 0\text{V}$	I_{GSS2}		± 200	nA dc
Drain current	3413	$V_{GS} = 0\text{V dc}$, bias condition C, $V_{DS} = 80$ percent of rated V_{DS}	I_{DSS2}		25	$\mu\text{A dc}$
Static drain to source "ON"-state resistance 2N7468U2 2N7469U2	3421	$V_{GS} = 12\text{V dc}$, condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(ON)3}$		0.011 0.022	Ω Ω
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$, $I_D = 1\text{ mA dc}$	$V_{GS(TH)2}$	1.0		V dc
Low temperature operation		$T_C = T_J = -55^\circ\text{C}$				
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS(TH)3}$, $I_D = 1\text{ mA dc}$	$V_{GS(TH)3}$		5.0	V dc
<u>Subgroup 4</u>						
Forward transconductance 2N7468U2 2N7469U2	3475	$I_D = I_{D2}$, $V_{DD} = 15\text{ V dc}$ (see 4.5.1)	g_{FS}	45 42		S S
Switching time test	3472	$I_D = I_{D2}$, $V_{GS} = 12\text{ V dc}$, $R_G = 2.35\ \Omega$, $V_{DD} = 50$ percent of rated V_{DS}				
Turn-on delay time 2N7468U2 2N7469U2			$t_{D(on)}$		35 35	ns ns
Rise time 2N7468U2 2N7469U2			t_r		125 125	ns ns
Turn-off delay time 2N7468U2 2N7469U2			$t_{D(off)}$		60 75	ns ns
Fall time 2N7468U2 2N7469U2			t_f		50 50	ns ns

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit			
	Method	Condition		Min	Max				
<u>Subgroup 5</u> Safe operating area test (high voltage)	3474	See figures 3, 4 and 5 $t_p = 10$ ms min. $V_{DS} = 80$ percent of max. rated V_{DS}							
Electrical measurements							See table I, group A, subgroup 2		
<u>Subgroup 6</u> Not applicable									
<u>Subgroup 7</u> Gate charge	3471	Condition B. $I_D = I_{D2}$, $V_{GS} = 12$ V dc $V_{DD} = 50$ percent of rated V_{DS}							
On-state gate charge 2N7468U2							$Q_{G(ON)}$	140	nC
2N7469U2								160	nC
Gate to source charge 2N7468U2							Q_{GS}	40	nC
2N7469U2								55	nC
Gate to drain charge 2N7468U2							Q_{GD}	40	nC
2N7469U2		65	nC						
Reverse recovery time	3473	$di/dt = -100$ A/ μ s, $V_{DD} \leq 50$ V $I_D = I_{D2}$							
2N7468U2							t_{rr}	200	ns
2N7469U2								300	ns

1/ For sampling plan, see MIL-PRF-19500.

2/ This test required for the following end-point measurements only:

Group B Subgroups 2 and 3 (JANTX, JANTXV).

Group B Subgroups 3 and 4 (JANS).

Group C, subgroup 6.

Group E, subgroup 1.

TABLE II. Group D inspection.

Inspection <u>1/ 2/ 3/</u>	MIL-STD-750		Symbol	Pre-irradiation limits		Post-irradiation limits				Unit
	Method	Conditions		R, F, G and H		R, F and G		H <u>4/</u>		
				Min	Max	Min	Max	Min	Max	
<u>Subgroup 1</u> Not applicable										
<u>Subgroup 2</u>		$T_C = + 25^\circ\text{C}$								
Steady-state total dose irradiation (VGS bias) <u>5/</u>	1019	$V_{GS} = 12\text{ V};$ $V_{DS} = 0\text{ V}$								
Steady-state total dose irradiation (VDS bias) <u>5/</u>	1019	$V_{GS} = 0\text{ V};$ $V_{DS} = 80\text{ percent of rated } V_{DS}(\text{preirradiation})$								
End-point electricals										
Breakdown voltage, drain to source 2N7468U2 2N7469U2	3407	$V_{GS} = 0\text{ V}; I_D = 1\text{ mA};$ bias condition C	$V_{(BR)DSS}$	60 100		60 100		60 100		V dc V dc
Gate to source voltage (threshold) 2N7468U2 2N7469U2	3403	$V_{DS} = V_{GS}$ $I_D = 1\text{ mA}$	$V_{GS(th)1}$	2.0 2.0	4.0 4.0	2.0 2.0	4.0 4.0	1.5 1.5	4.0 4.0	V dc V dc
Gate current	3411	$V_{GS} = +20\text{ V}; V_{DS} = 0\text{ V}$ Bias condition C	I_{GSSF1}		100		100		100	nA dc
Gate current	3411	$V_{GS} = -20\text{ V}; V_{DS} = 0\text{ V}$ Bias condition C	I_{GSSR1}		-100		-100		-100	nA dc
Drain current	3413	$V_{GS} = 0\text{ V}$ $V_{DS} = 80\text{ percent of rated } V_{DS}$ (preirradiation); bias condition C	I_{DSS}		10		10		10	$\mu\text{A dc}$
Static drain to source on-state voltage 2N7468U2 2N7469U2	3405	$V_{GS} = 12\text{ V}; I_D = I_{D2};$ condition A; pulsed (see 4.5.1)	$V_{DS(on)}$		0.275 0.585		0.275 0.585		0.343 0.731	V dc V dc
Forward voltage source drain diode 2N7468U2 2N7469U2	4011	$V_{GS} = 0\text{ V}; I_D = I_{D1};$ bias condition C	V_{SD}		1.3 1.2		1.3 1.2		1.3 1.2	V dc V dc

1/ For sampling plan see MIL-PRF-19500.

2/ Group D qualification may be performed prior to lot formation. Wafers qualified to these group D QCI requirements may be used for any other detail specification utilizing the same die design.

3/ At the manufacturer's option, group D samples need not be subjected to the screening tests, and may be assembled in it's qualified package or in any qualified package that the manufacturer has data to correlate the performance to the designated package.

4/ The H designation represents devices which pass endpoints at all 100K, 300K and 600K rads (Si).

5/ Separate samples shall be pulled for each bias.

TABLE III. Group E inspection (all quality levels) - for qualification only.

Inspection	MIL-STD-750		Qualification inspection
	Method	Conditions	
<u>Subgroup 1</u>			12 devices c = 0
Temperature cycling	1051	Test condition G, 500 cycles	
Hermetic seal	1071		
Fine leak			
Gross leak			
Electrical measurements		See table I, group A, subgroup 2	
<u>Subgroup 2 1/</u>			12 devices c = 0
Steady-state gate bias	1042	Test condition B; 1,000 hours	
Electrical measurements		See table I, group A, subgroup 2	
Steady-state reverse bias	1042	Test condition A; 1,000 hours	
Electrical measurements		See table I, group A, subgroup 2	
<u>Subgroup 3</u>			
Not applicable			
<u>Subgroup 4</u>			12 devices c = 0
Thermal resistance	3161	$R_{\theta JC} = 0.50^{\circ}\text{C/W}$ maximum. See 4.5.2	
<u>Subgroup 5</u>			
Not applicable			
<u>Subgroup 6</u>			3 devices c = 0
ESD	1020		
Electrical measurements		See table I, group A, subgroup 2	

See footnotes at end of table.

TABLE III. Group E inspection (all quality levels) - for qualification only - Continued.

Inspection	MIL-STD-750		Qualification and large lot quality conformance inspection
	Method	Conditions	
<u>Subgroup 7</u> SEE <u>2/ 3/ 4/</u> Electrical measurements <u>5/</u> SEE irradiation 2N7468U2 2N7469U2 2N7468U2 2N7469U2 2N7468U2 2N7469U2	1080	IGSS1 and IDSS1 in accordance with table I, group A, subgroup 2 Fluence = $3E5 \pm 20$ percent ions/cm ² Flux = $2E3$ to $2E4$ ions/cm ² /sec, temperature = $25 \pm 5^\circ C$ LET = $37 \text{ MeV-cm}^2/\text{mg}$, Range = 39 microns, Energy = 305 MeV Insitu bias conditions: VDS = 60V & VGS = -20V Insitu bias conditions: VDS = 100V & VGS = -20V LET = $60 \text{ MeV-cm}^2/\text{mg}$, Range = 32 microns, Energy = 340 MeV Insitu bias conditions: VDS = 46V & VGS = -5V VDS = 35V & VGS = -10V VDS = 25V & VGS = -15V VDS = 15V & VGS = -20V Insitu bias conditions: VDS = 100V & VGS = -10V VDS = 35V & VGS = -15V VDS = 25V & VGS = -20V LET = $82 \text{ MeV-cm}^2/\text{mg}$, Range = 28 microns, Energy = 350 MeV Insitu bias conditions: VDS = 35V & VGS = -5V VDS = 27V & VGS = -10V VDS = 20V & VGS = -15V VDS = 14V & VGS = -20V Insitu bias conditions: VDS = 100V & VGS = -5V VDS = 80V & VGS = -10V VDS = 25V & VGS = -15V	3 devices
Electrical measurements <u>2/</u>		IGSS1 and IDSS1 in accordance with table I, group A, subgroup 2	

- 1/ A separate sample for each test shall be pulled.
- 2/ Group E qualification of single event effect testing may be performed prior to lot formation. Qualification may be extended to other performance specifications utilizing the same structurally identical die design.
- 3/ Device qualification to a higher level LET is sufficient to qualify all lower level LET's.
- 4/ The sampling plan applies to each bias condition.
- 5/ Examine IGSS1 and IDSS1 before and following SEE irradiation to determine acceptability for each bias condition. Other test conditions in accordance with table I, group A, subgroup 2, may be performed at the manufacturer's option.

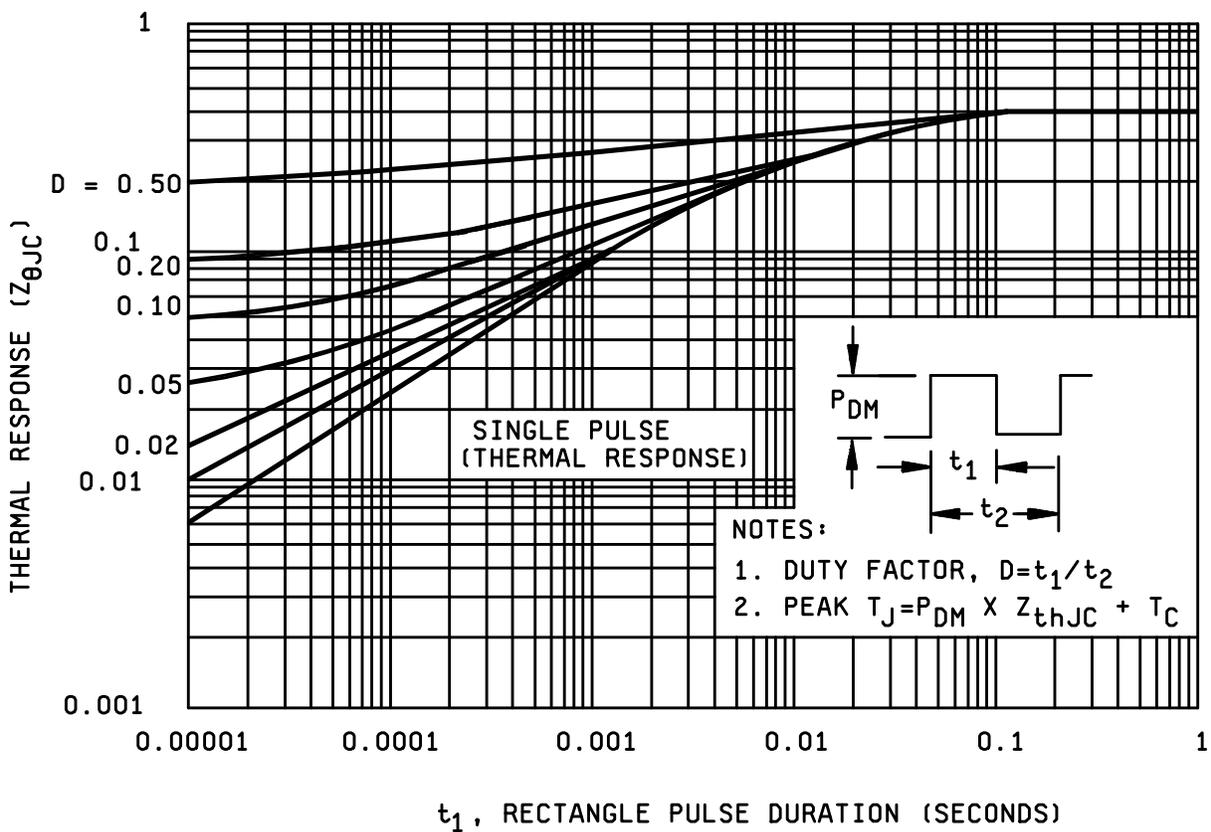


FIGURE 2. Thermal response curve.

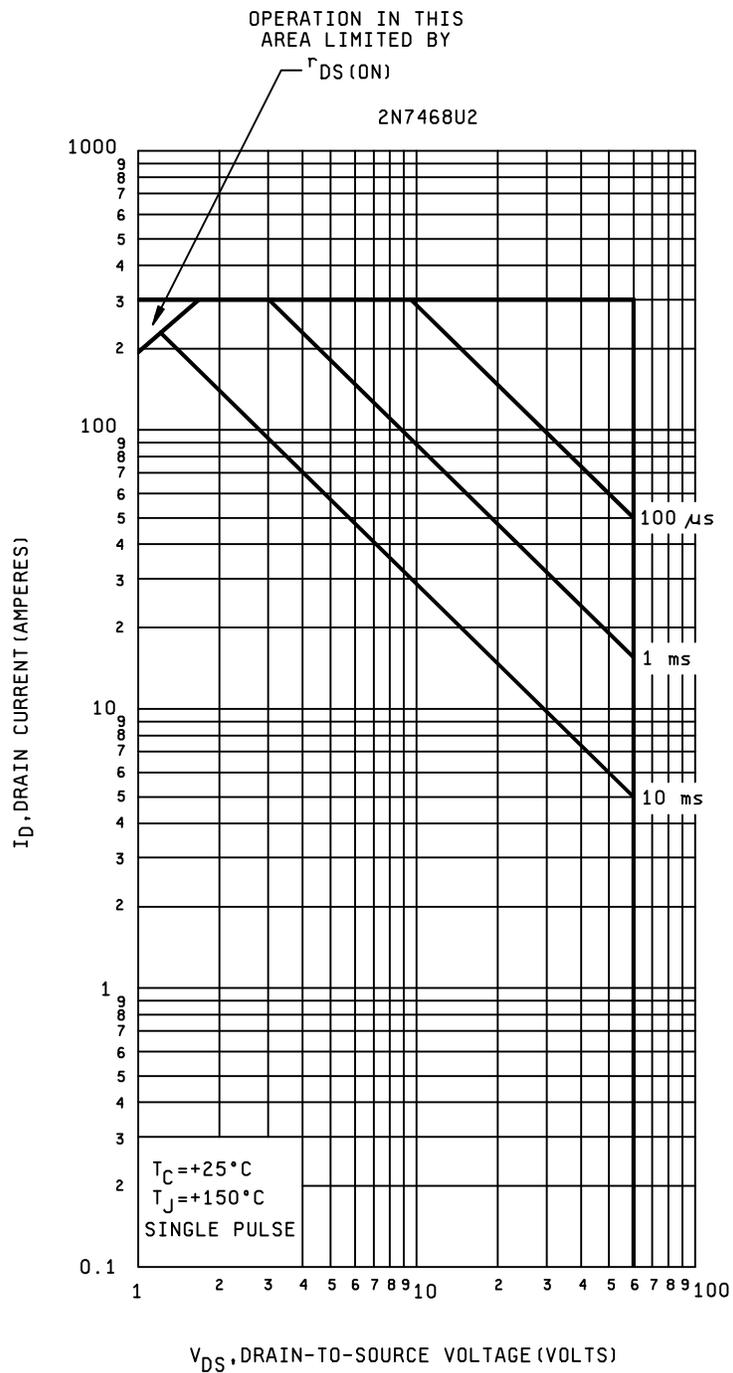


FIGURE 3. Safe operating area graph.

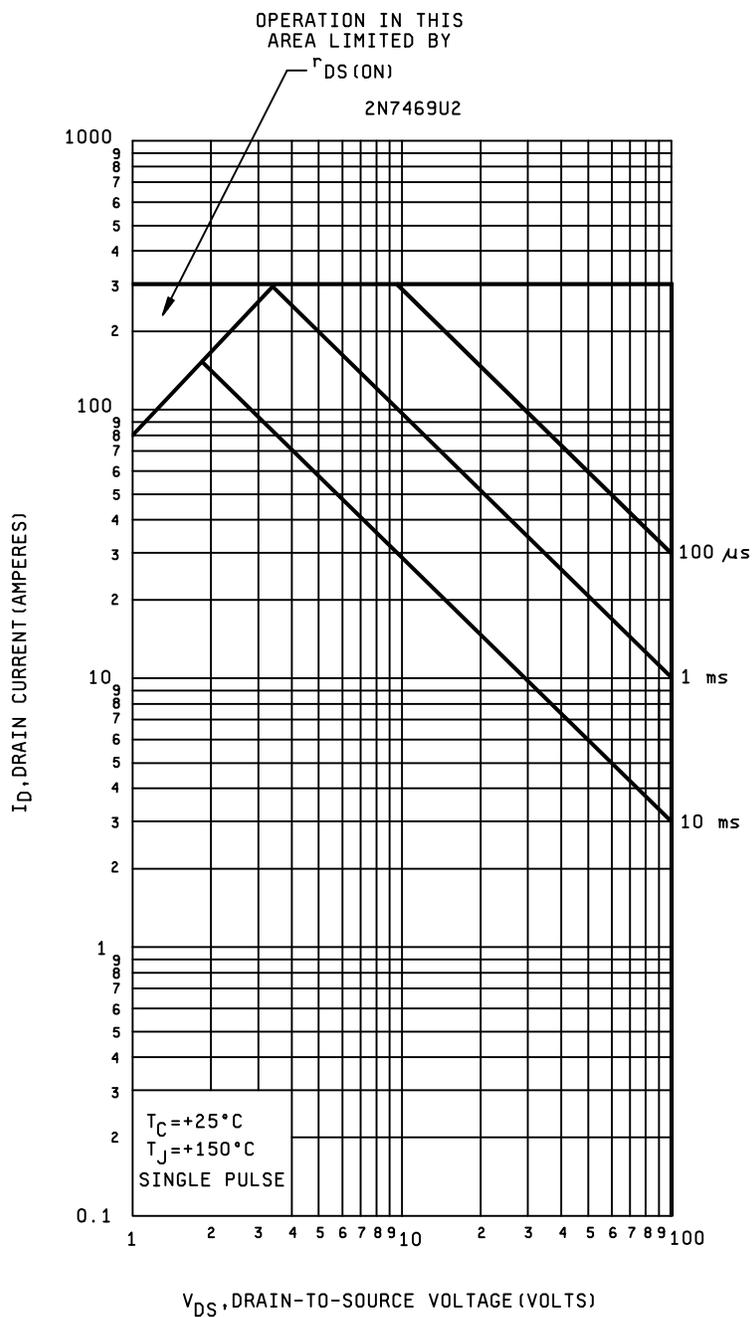
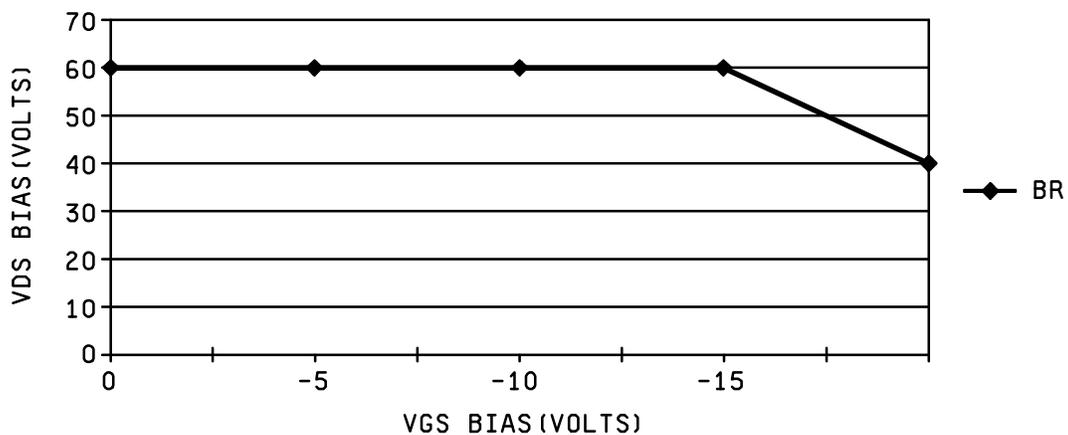


FIGURE 4. Safe operating area graph.

2N7468U2



2N7469U2

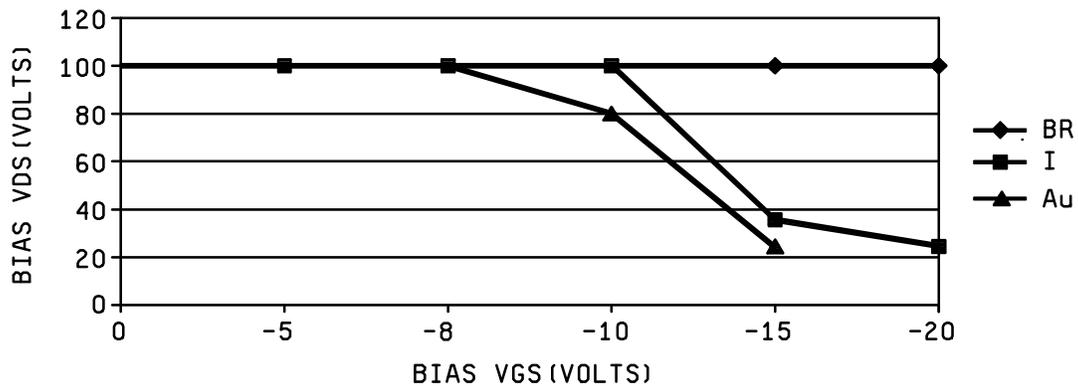


FIGURE 5. SEE safe operating area graph.

4.5.5 Gate stress test.

- a. $V_{GS} = 24$ V, minimum.
- b. $t = 250$ μ S, minimum.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Points' packaging activity within the Military Department or Defense Agency, or within the Military Departments' System Command. Packaging data retrieval is available from the managing Military Departments' or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Intended use. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. Acquisition documents must specify the following:

- a. Title, number, and date of this specification.
- b. Issue of DoDISS to be cited in the solicitation and, if required, the specific issue of individual documents referenced (see 2.2.1).
- c. Terminal finish (see 3.4.1).
- d. Type designation and product assurance level.
- e. Packaging requirements (see 5.1).

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-19500 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center Columbus, ATTN: DSCC-VQE, P.O. Box 3990, Columbus, OH 43216-5000.

6.4 Substitution information. The following table shows the generic P/N and its associated military P/N (without JAN and RHA prefix).

Generic P/N	Military P/N
IRHNA57064	2N7468U2
IRHNA57160	2N7469U2

MIL-PRF-19500/673

Custodians:
Army - CR
Navy - NW
Air Force - 11
NASA - NA
DLA - CC

Preparing activity:
DLA - CC

(Project 5961-2396)

STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL

INSTRUCTIONS

1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.
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3. The preparing activity must provide a reply within 30 days from receipt of the form.

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I RECOMMEND A CHANGE:	1. DOCUMENT NUMBER MIL-PRF-19500/673	2. DOCUMENT DATE 9 March 2001
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3. DOCUMENT TITLE
SEMICONDUCTOR DEVICE, FIELD EFFECT RADIATION HARDENED (TOTAL DOSE AND SINGLE EVENT EFFECTS) TRANSISTOR, N-CHANNEL, SILICON TYPES 2N7468U2 and 2N7469U2 JANTXVR, F, G AND H AND JANSR, F, G AND H

4. NATURE OF CHANGE (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)

5. REASON FOR RECOMMENDATION

6. SUBMITTER

a. NAME (Last, First, Middle initial)	b. ORGANIZATION		
c. ADDRESS (Include Zip Code)	d. TELEPHONE (Include Area Code)	7. DATE SUBMITTED	
	COMMERCIAL DSN FAX EMAIL		

8. PREPARING ACTIVITY

a. Point of Contact Alan Barone	b. TELEPHONE Commercial DSN FAX EMAIL 614-692-0510 850-0510 614-692-6939 alan.barone@dscclia.mil
c. ADDRESS Defense Supply Center Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43216-5000	IF YOU DO NOT RECEIVE A REPLY WITHIN 45 DAYS, CONTACT: Defense Standardization Program Office (DLSC-LM) 8725 John J. Kingman, Suite 2533, Fort Belvoir, VA 22060-6221 Telephone (703) 767-6888 DSN 427-6888